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### FGA30N60LSD 600 V, 30 A PT IGBT

#### Features

- Low Saturation Voltage: V<sub>CE(sat)</sub> = 1.1 V @ I<sub>C</sub> = 30 A
- High Input Impedance
- Low Conduction Loss

#### **Applications**

Solar Inverter, UPS

#### November 2013

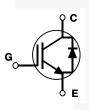


FGA30N60LSD — 600 V, 30 A PT IGBT

### **General Description**

Using Fairchild's advanced PT technology, the FGA30N60LSD IGBT offers superior conduction performances, which offer the optimum performance for medium switching application such as solar inverter, UPS applications where low conduction losses are the most important factor.





#### **Absolute Maximum Ratings**

Symbol	Description		Ratings	Unit	
V <sub>CES</sub>	Collector-Emitter Voltage		600	V	
V <sub>GES</sub>	Gate-Emitter Voltage		± 20	V	
I <sub>C</sub>	Collector Current	@ T <sub>C</sub> = 25°C	60	A	
	Collector Current	@ T <sub>C</sub> = 100°C	30	A	
I <sub>CM (1)</sub>	Pulsed Collector Current	90	А		
I <sub>FSM</sub>	Non-repetitive Peak Surge Current 60Hz Single Half-Sine Wave		150	A	
P <sub>D</sub>	Maximum Power Dissipation $@T_{C} = 25^{\circ}C$		480	W	
	Maximum Power Dissipation	@ T <sub>C</sub> = 100°C	192	W	
TJ	Operating Junction Temperature		-55 to +150	°C	
T <sub>stg</sub>	Storage Temperature Range		-55 to +150	°C	
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C	

Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

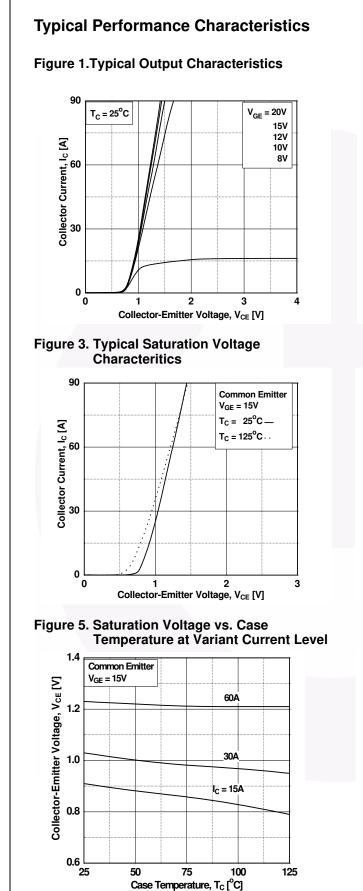
#### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction-to-Case		0.26	°C/W
$R_{\theta JC}(Diode)$	Thermal Resistance, Junction-to-Case		0.92	°C/W
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction-to-Ambient		40	°C/W

Part NumberTop MarkPackageFGA30N60LSDTUFGA30N60LSDTO-3P		Top Mark	Package	Packing Method	Reel Size	Tape Width		Quantity	
		Tube	N/A	N/A		30			
Electric	al Cha	racteristics	of the IG	<b>BT</b> T <sub>C</sub> = 25°C unless otherw	ise noted				
Symbol		Parameter		Test Condition	s Min.	Тур.	Max	. Unit	
Off Charac	toristics					ł	+		
BV <sub>CES</sub>	Collector-Emitter Breakdown Voltage		n Voltage	V <sub>GE</sub> = 0 V, I <sub>C</sub> = 250 uA	600			V	
$\Delta B_{VCES}/\Delta T_J$	Temperature Coefficient of Breakdown Voltage		0	$V_{GE} = 0 V, I_C = 250 uA$		0.6		V/°C	
I <sub>CES</sub>		r Cut-Off Current		V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0 V			250	uA	
I <sub>GES</sub>		kage Current		$V_{GE} = V_{GES}, V_{CE} = 0 V$			±250	nA	
							1	I	
On Charac V <sub>GE(th)</sub>	1	eshold Voltage		I <sub>C</sub> = 250 uA, V <sub>CE</sub> = V <sub>GE</sub>	4.0	5.5	7.0	V	
GE(th)		contracted voltage		$I_{\rm C} = 30$ A, $V_{\rm GE} = 15$ V		1.1	1.4	V	
V <sub>CE(sat)</sub>	Saturation Voltage		-	$I_{C} = 30 \text{ A}, V_{GE} = 15 \text{ V},$ $T_{C} = 125^{\circ}\text{C}$	-	1.0		V	
			I <sub>C</sub> = 60 A, V <sub>GE</sub> = 15 V		1.3		V		
Dynamic C	haracteri	stics							
C <sub>ies</sub>	Input Capacitance					3550		pF	
C <sub>oes</sub>	Output C	utput Capacitance		V <sub>CE</sub> = 30 V <sub>,</sub> V <sub>GE</sub> = 0 V, f = 1 MHz		245		pF	
C <sub>res</sub>	Reverse Transfer Capacitance				90		pF		
Switching	Characte	rietice							
t <sub>d(on)</sub>		Delay Time				18		ns	
t <sub>r</sub>	Rise Time				46		ns		
t <sub>d(off)</sub>	Turn-Off	Delay Time		V <sub>CC</sub> = 400 V, I <sub>C</sub> = 30 A,		250		ns	
t <sub>f</sub>	Fall Time	9		$R_{G} = 6.8 \Omega, V_{GE} = 15 V,$		1.3	2.0	us	
E <sub>on</sub>	Turn-On	Switching Loss		Inductive Load, $T_C = 25^{\circ}C$		1.1		mJ	
E <sub>off</sub>	Turn-Off	Switching Loss				21		mJ	
t <sub>d(on)</sub>	Turn-On	Delay Time				17		ns	
t <sub>r</sub>	Rise Time					45		ns	
t <sub>d(off)</sub>	Turn-Off	Delay Time		V <sub>CC</sub> = 400 V, I <sub>C</sub> = 30 A,		270		ns	
t <sub>f</sub>	Fall Time		$R_{G} = 6.8 \Omega$ , $V_{GE} = 15 V$ ,		2.6		us		
E <sub>on</sub>	Turn-On	Switching Loss		Inductive Load, T <sub>C</sub> = 125°		1.1		mJ	
E <sub>off</sub>	Turn-Off	Switching Loss				36		mJ	
Qg	Total Ga	te Charge				225		nC	
Q <sub>ge</sub>	Gate-Em	nitter Charge		$V_{CE} = 300 \text{ V}, \text{ I}_{C} = 30 \text{ A},$ $V_{GE} = 15 \text{ V}$		30		nC	
Q <sub>gc</sub>	Gate-Co	llector Charge		-GE - 10 -		105		nC	
Le	Internal	Emitter Inductance		Measured 5mm from PKG	à	7		nH	

Parameter	Conditions		Min.	Тур.	Max	Unit	
V <sub>FM</sub>	I <sub>F</sub> = 15 A I <sub>F</sub> = 15 A	T <sub>C</sub> = 25 °C T <sub>C</sub> = 125 °C	-	1.8 1.6	2.2	V V	
I <sub>RM</sub>	V <sub>R</sub> = 600 V	T <sub>C</sub> = 25 °C	-	-	100	μA	
t <sub>rr</sub>	I <sub>F</sub> =1 A, di <sub>F</sub> /dt = 100 A/μs, V <sub>R</sub> = 30 V I <sub>F</sub> =15 A, di <sub>F</sub> /dt = 100 A/μs, V <sub>R</sub> = 390 V	T <sub>C</sub> = 25 °C T <sub>C</sub> = 25 °C	-	- -	35 40	ns ns	
t <sub>a</sub> t <sub>b</sub> Q <sub>rr</sub>	I <sub>F</sub> =15 A, di <sub>F</sub> /dt = 100 A/μs, V <sub>R</sub> = 390 V	$T_{C} = 25 \degree C$ $T_{C} = 25 \degree C$ $T_{C} = 25 \degree C$	- -	18 13 27.5	- - -	ns ns nC	

#### Electrical Characteristics of the Diode T<sub>c</sub> = 25°C unless otherwise noted



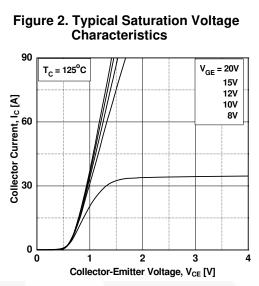


Figure 4. Transfer characteristics

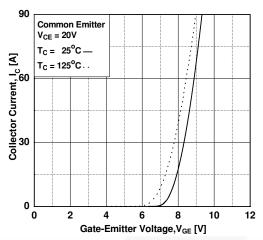
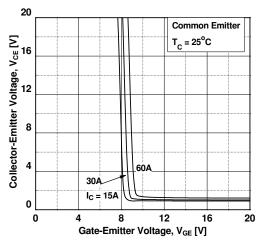
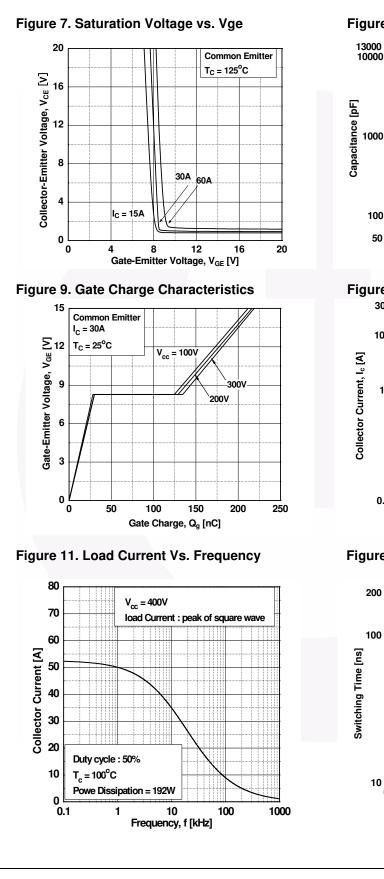


Figure 6. Saturation Voltage vs. Vge



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Typical Performance Characteristics (Continued)

Figure 8. Capacitance characteristics

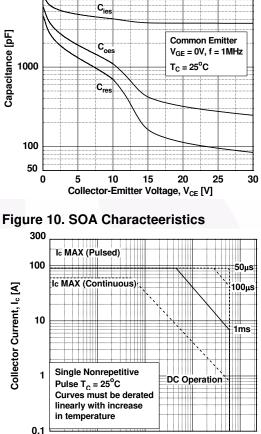
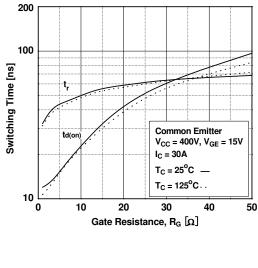


Figure 12. Turn-On Characteristics vs. Gate Resistance

. 0.1 1 10 100 Collector-Emitter Voltage, V<sub>CE</sub> [V]

1000



t,

t<sub>d(on)</sub>

70

80

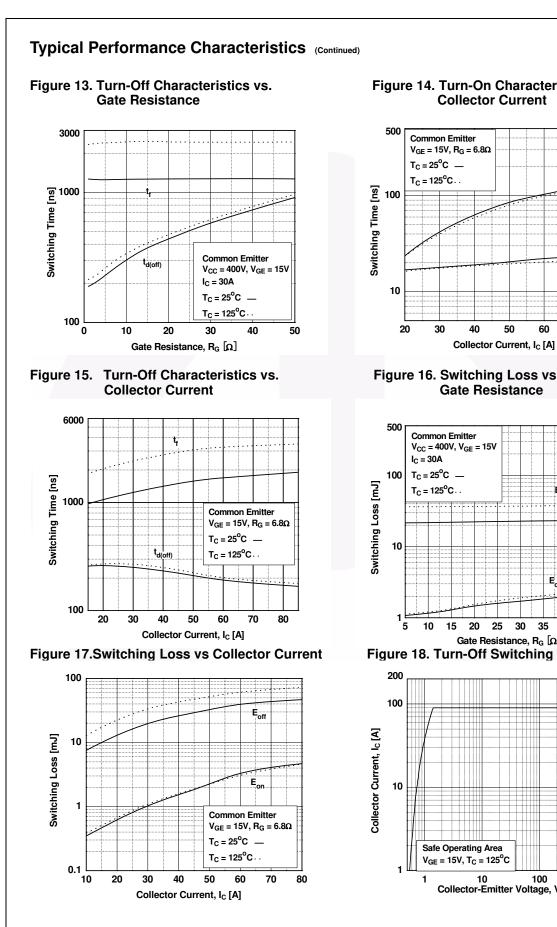
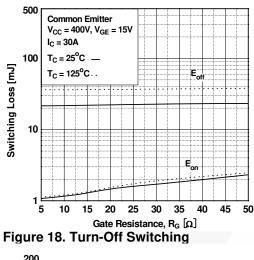
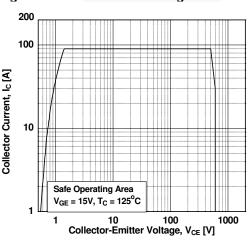


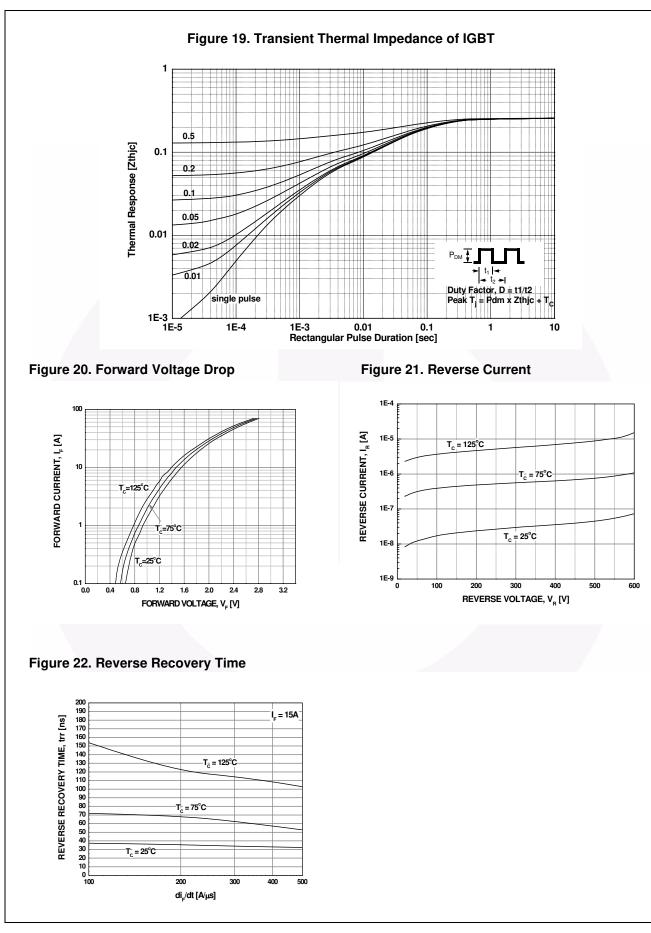
Figure 14. Turn-On Characteristics vs. **Collector Current** 



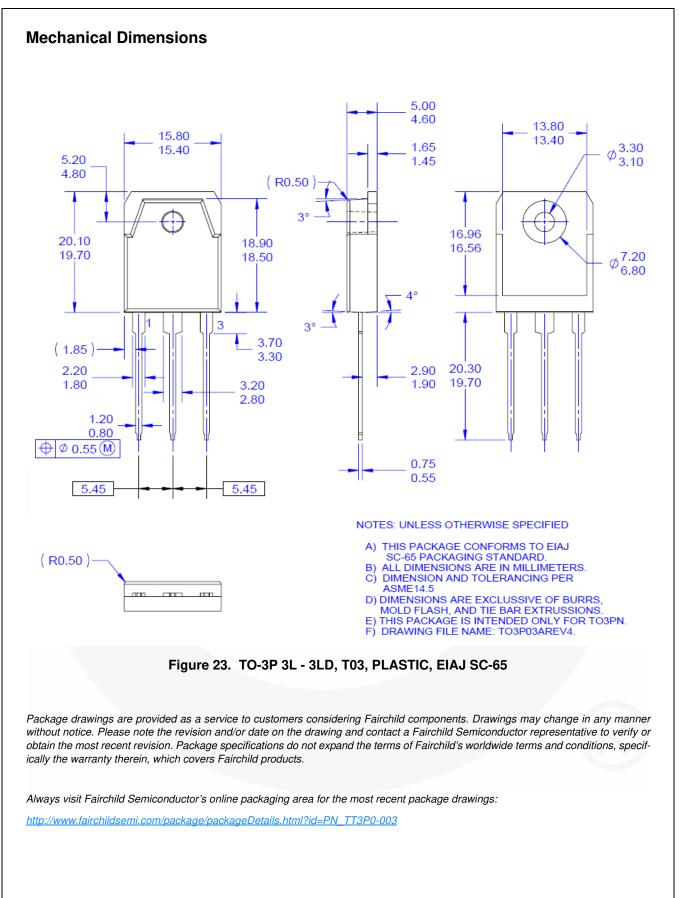
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60





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